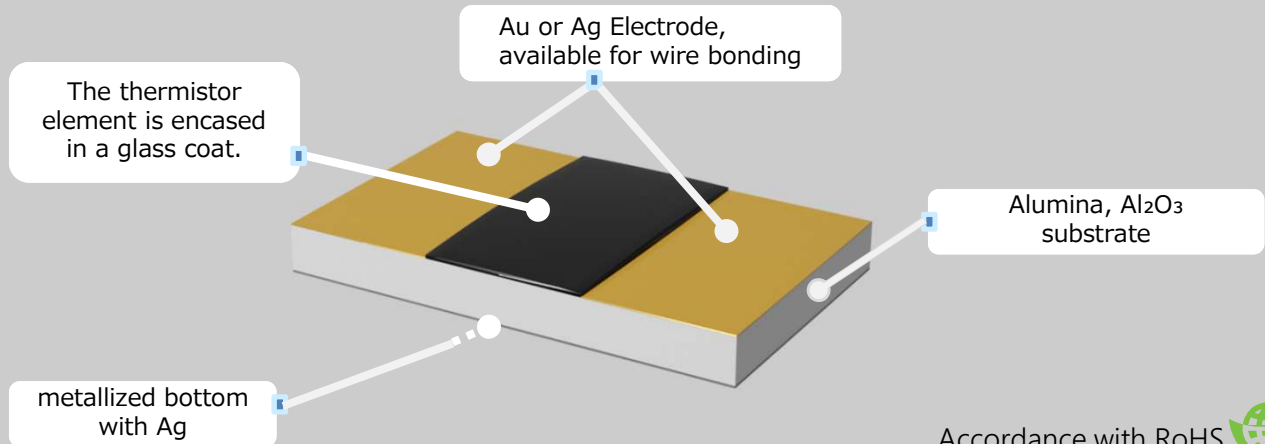




The world's pioneering product.

Thick Film Chip Thermistor Rated for 200°C for Wire Bonding

Crafted through ingenious material design, precision mixing processes, and safeguarded by patent protection.



Accordance with RoHS

Features

- Optimized for high temperature sensing, control, and compensation.
- Wide temperature ranges from -40°C to +200°C are ideal for SiC and GaN.
- The top surface has two electrodes Au or Ag perfectly suitable for wire bonding.
- The bottom surface is metallized with Ag for sintering.
- Empowered by an Alumina base and Glass coating, ensuring high mechanical strength.
- Unparalleled thermal responsiveness due to its compact cubic volume and exceptional heat capacity.
- Thermal Response: Featuring minimal thermal capacity, yet heightened sensor sensitivity.
- AEC-Q200 compliant product.

Application

- SiC/GaN Power modules
- Inverter for EV and HEV Vehicles
- IGBT (Insulated Gate Bipolar Transistor)
- MOSFET (Metal-Oxide-Semiconductor Field-Effect Transistor)
- DC-DC Converter
- Temperature management of the On-Board Charger
- Temperature compensation of semiconductors
- Automotive ABS control circuit

The product characteristics can be customized according to customer requirements. Please feel free to contact us.

Specification data

Chip size (mm)	Operating temperature	Resistance at 25°C	B Constance	Rated power	Maximum permissible power	Thermal dissipation constant (in air)	Thermal time constant (In air)	Electrode
1608	-40°C to +200°C	1k to 500kΩ	3375 to 4500K	120mW	5mW	δ≤1.5mW/°C	τ≤5sec	Au,Ag
2012		500 to 400kΩ		130mW				
3216		500 to 400kΩ		130mW				

